

Application No. 10/707,842

Applicant: Haining S. YANG et al.

Title: METHOD AND APPARATUS FOR INCREASE STRAIN EFFECT
IN A TRANSISTOR CHANNEL

Responsive to Official Communication dated: December 27, 2005

REPLACEMENT SHEET

IAP7 Rec'd PCT/PTO 28 AUG 2006

Confirmation No. 1841

Attorney Docket No. P27165

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FIG. 1

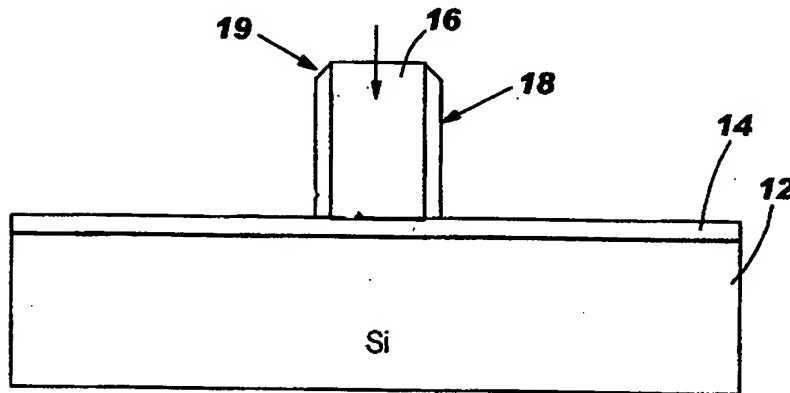
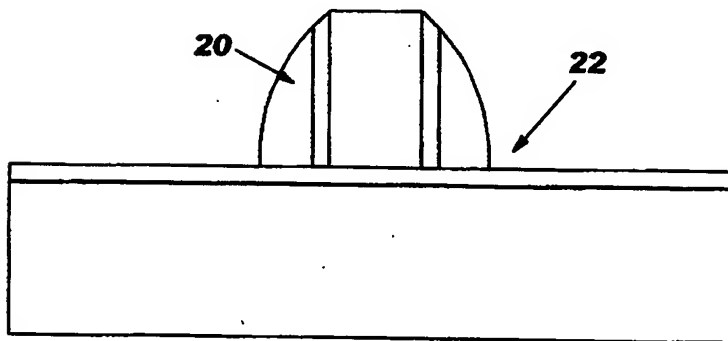


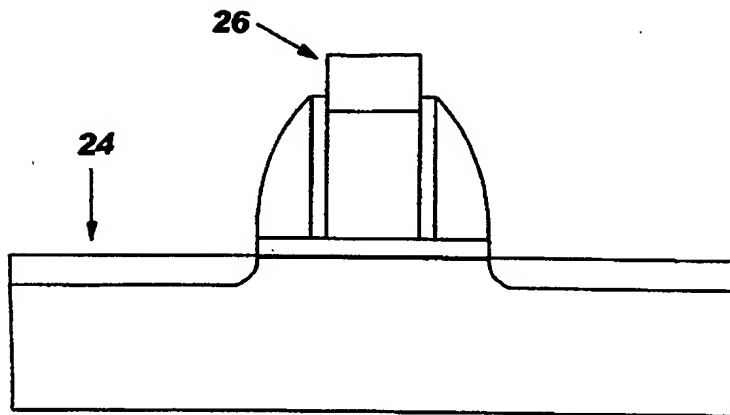
FIG. 2



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FIG. 3



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FIG. 4

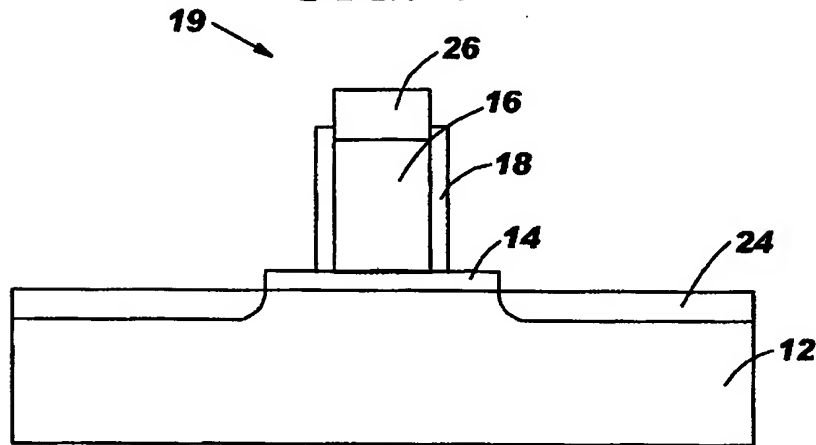
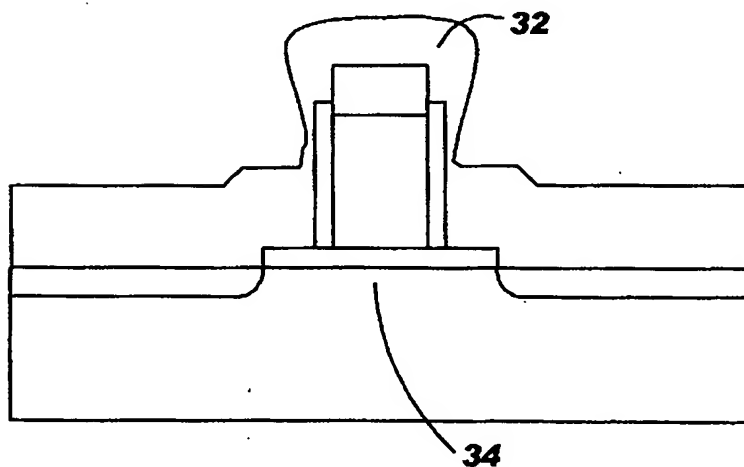


FIG. 5



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FIG. 6

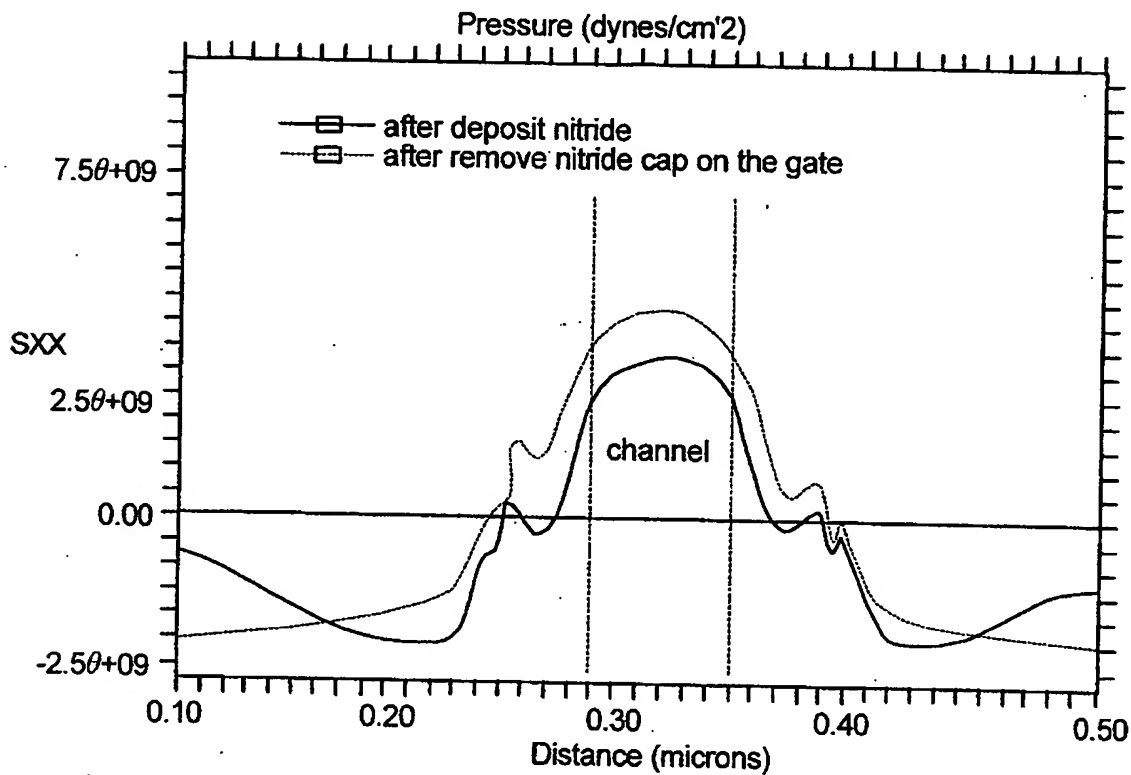
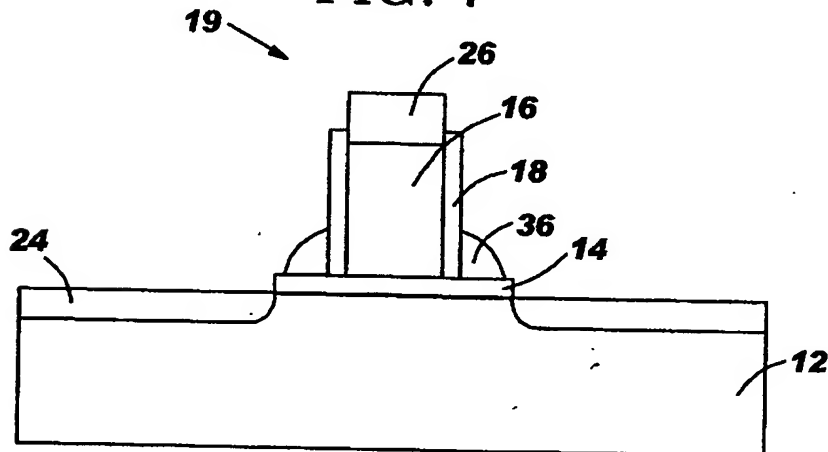


FIG. 7



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FIG. 8

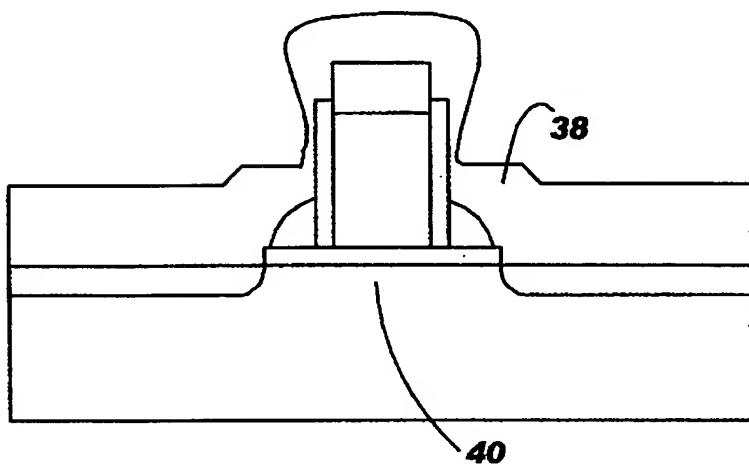
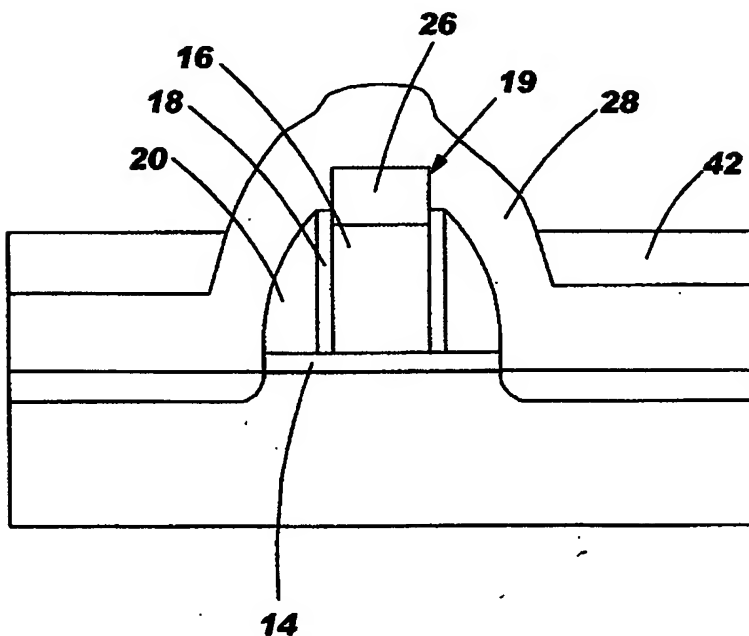


FIG. 9



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A cross-sectional view of a semiconductor device. A central structure, labeled 42, is positioned on a substrate, labeled 28. The structure 42 consists of a central rectangular block with two smaller rectangular blocks on either side, all resting on a common base layer. The substrate 28 is a thick, uniform layer at the bottom. The central structure 42 is flanked by two trapezoidal regions that taper downwards into the substrate.

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FIG. 12

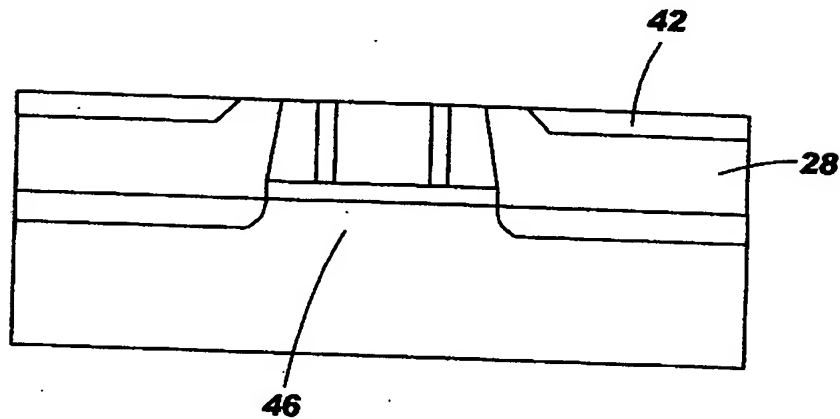
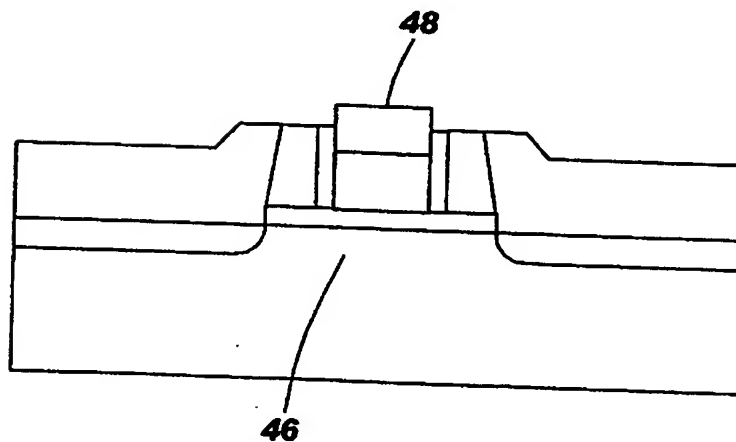


FIG. 13



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